

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
100V	280mΩ@10V	2A
	310mΩ@4.5V	

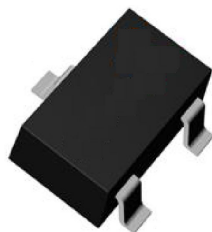
Feature

- Advanced trench process technology
- High density cell design for ultra low on-resistance
- Suffix "-Q1" for AEC-Q101

Application

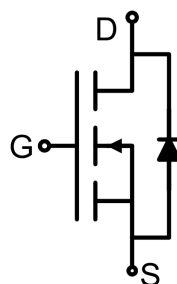
- Load Switch for Portable Devices
- DC/DC Converter

Package

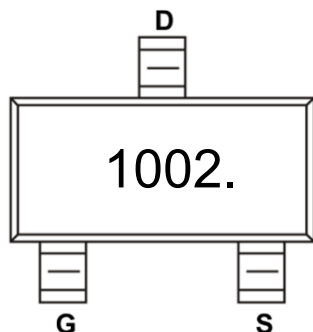


SOT-23

Circuit diagram



Marking



Absolute maximum ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	2	A
Pulsed Drain Current	I_{DM}	8	A
Power Dissipation	P_D	1.2	W
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Electrical characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.1		3.0	V
Drain-source on-resistance ¹⁾	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 2A$			280	m Ω
		$V_{GS} = 4.5V, I_D = 1A$			310	
Dynamic characteristics ²⁾						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		387		pF
Output Capacitance	C_{oss}			31		
Reverse Transfer Capacitance	C_{rss}			28		
Total Gate Charge	Q_g	$V_{DS} = 50V, V_{GS} = 10V, I_D = 2A$		9.56		nC
Gate-Source Charge	Q_{gs}			1.81		
Gate-Drain Charge	Q_{gd}			1.97		
Turn-on delay time	$t_{d(on)}$	$V_{DS} = 50V, V_{GS} = 10V, I_D = 1.3A, R_{GEN} = 1\Omega$		4		nS
Turn-on rise time	t_r			17.8		
Turn-off delay time	$t_{d(off)}$			13.2		
Turn-off fall time	t_f			28		
Source-Drain Diode characteristics						
Diode Forward Current ¹⁾	I_S				2.0	A
Diode Forward voltage	V_{SD}	$V_{GS} = 0V, I_S = 2A$			1.2	V

Notes:

1) Pulse Test: Pulse Width < 300 μs , Duty Cycle $\leq 2\%$.

2) Guaranteed by design, not subject to production testing.

Typical Characteristics

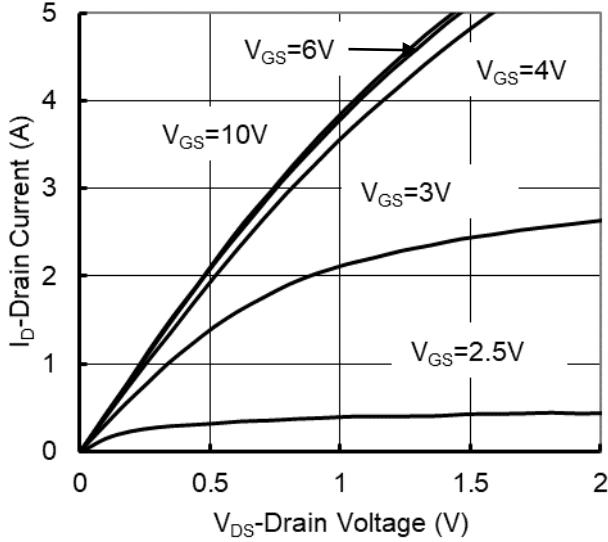


Figure1. Output Characteristics

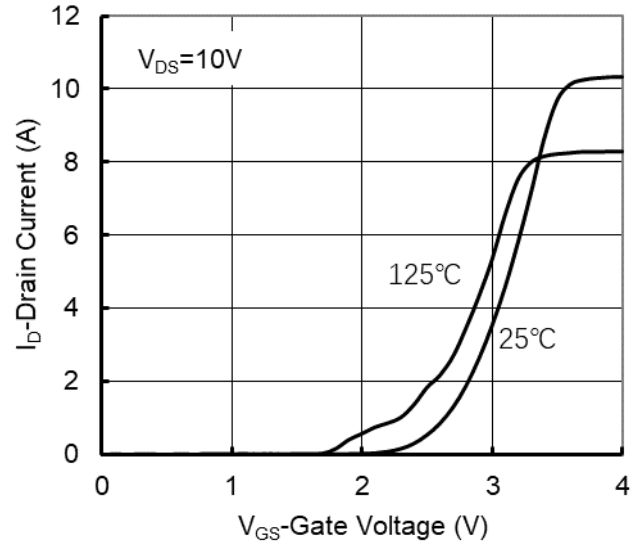


Figure2. Transfer Characteristics

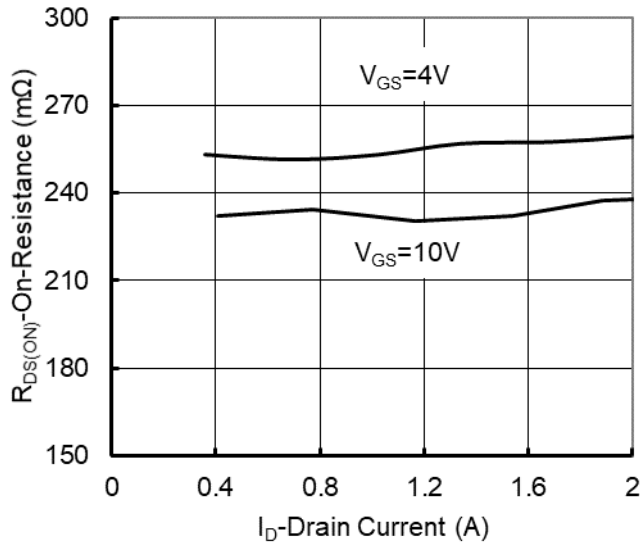


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

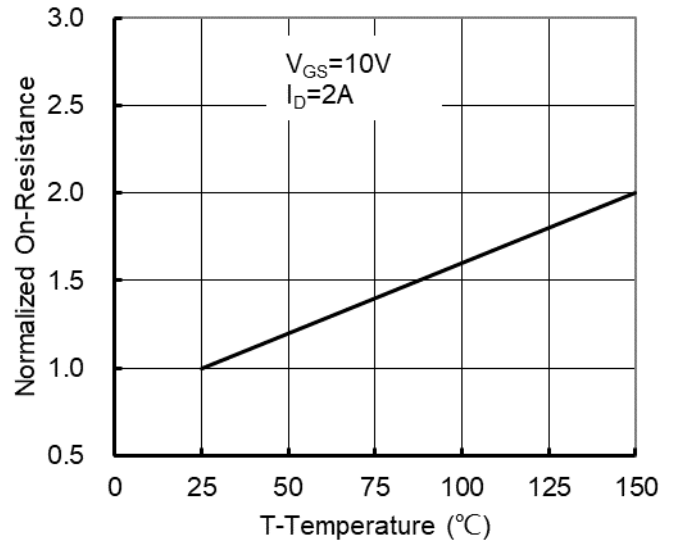


Figure 4: On-Resistance vs. Junction Temperature

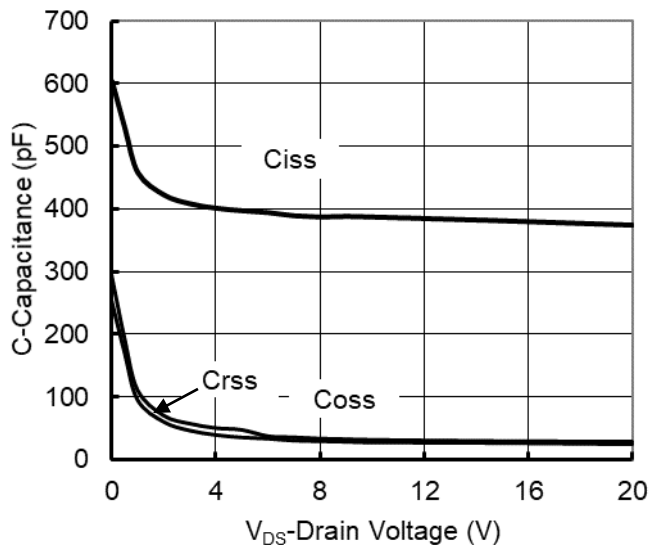


Figure5. Capacitance Characteristics

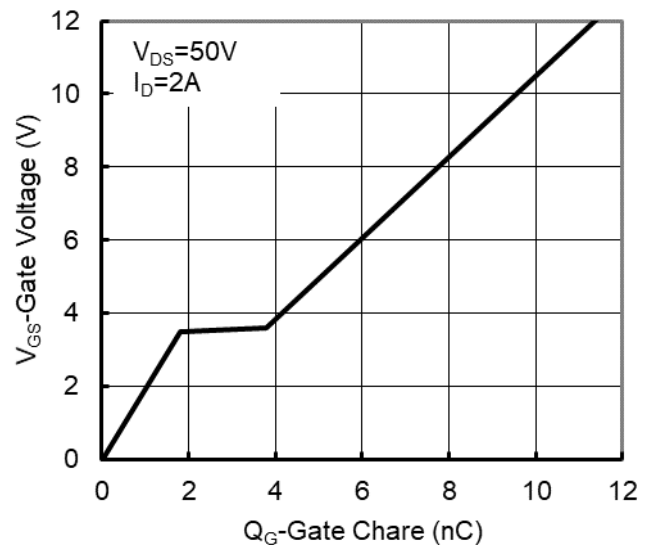


Figure6. Gate Charge

Typical Characteristics

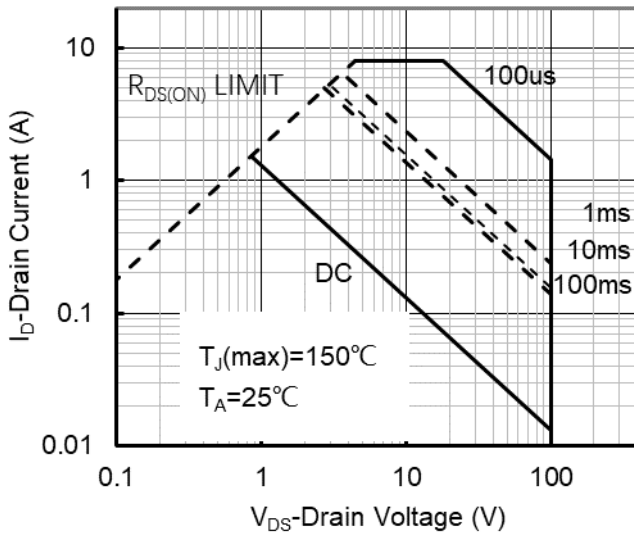


Figure7. Safe Operation Area

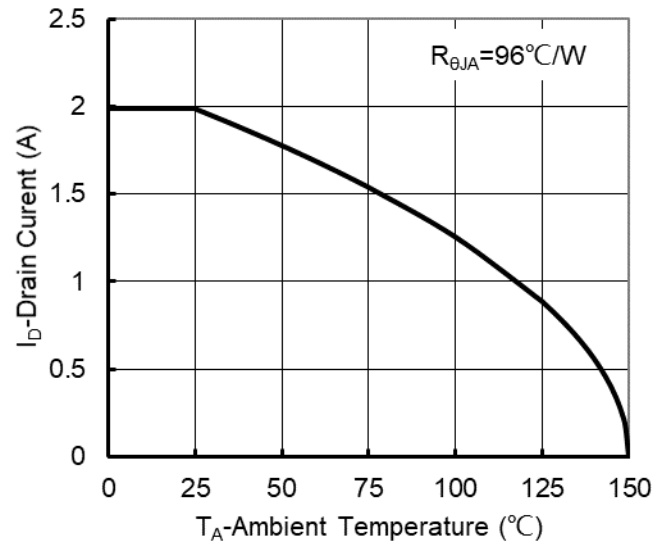


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

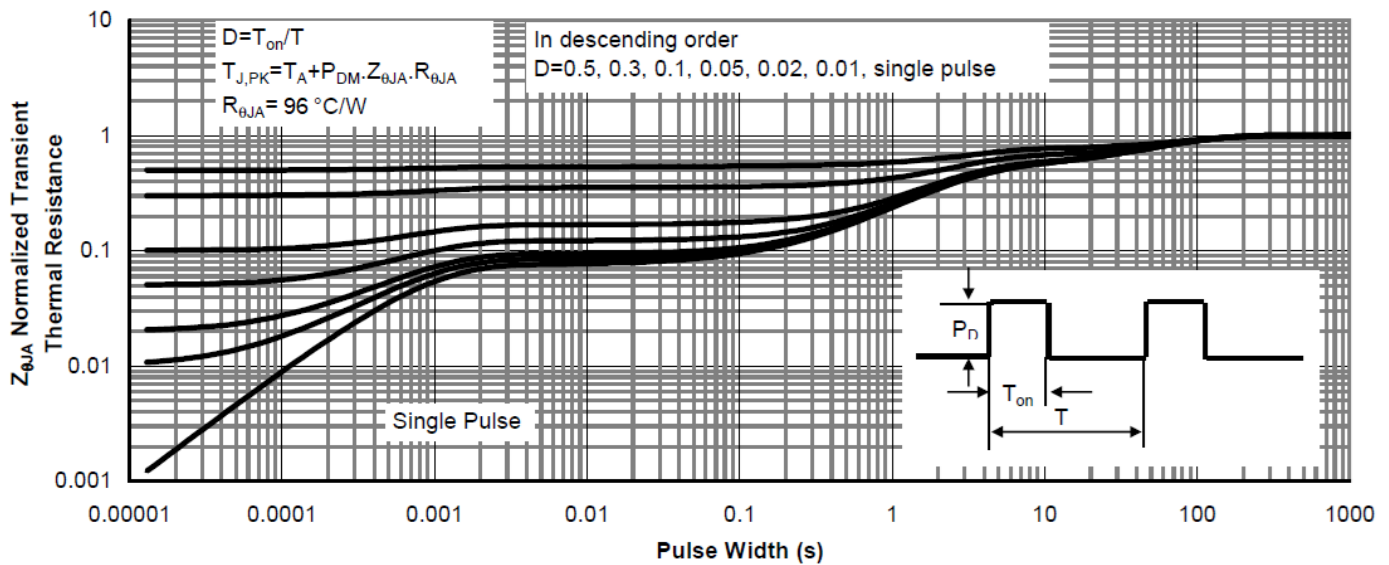
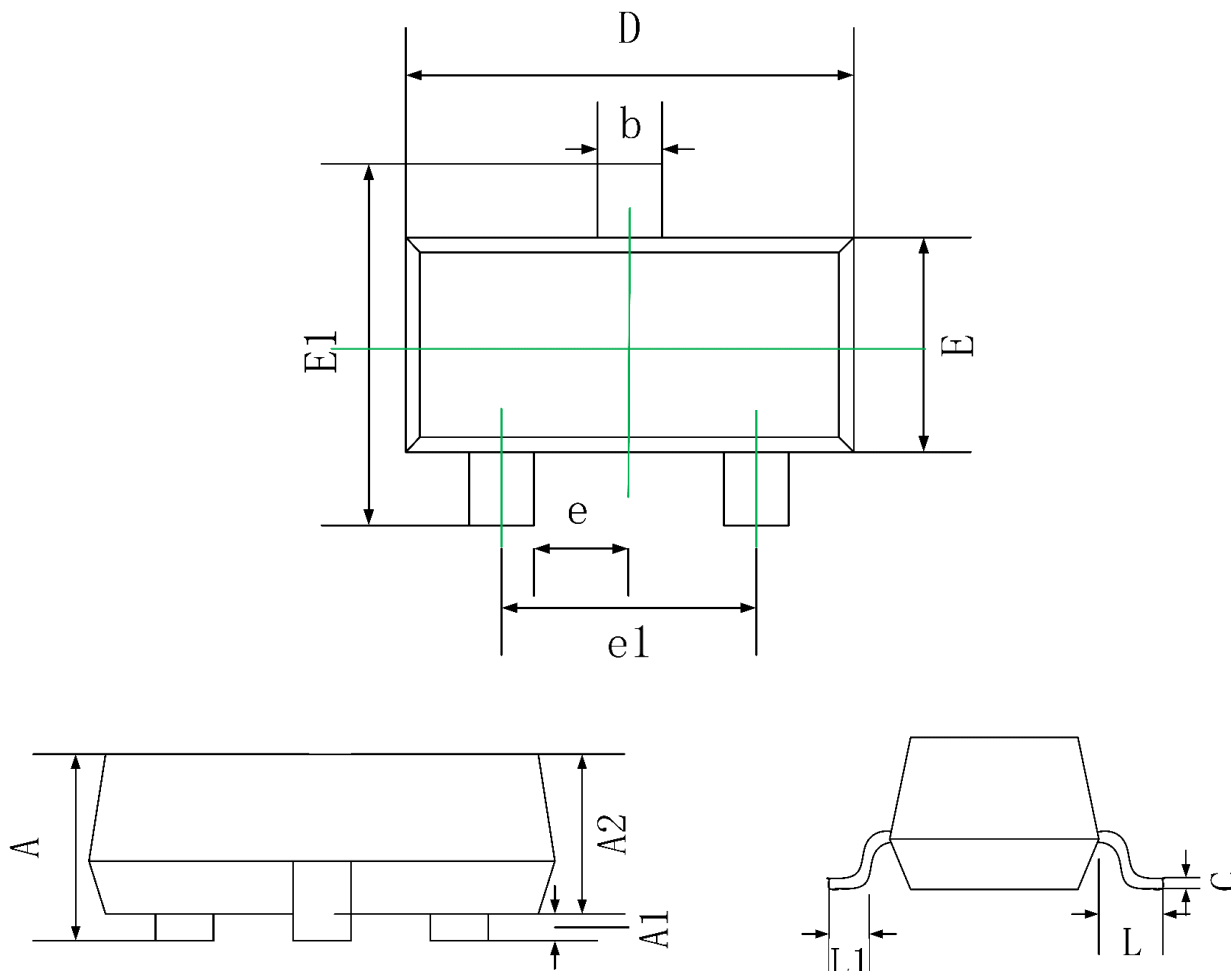


Figure9. Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.200	0.003	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020